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022204			EXAMINER	
PIXIN FEARODY, LLF			MULEMURI, S	
2180 GREENSBORO DRIVE			ART UNIT	PAPER NUMBER
SUITE 800 MCLEAN VA 22102			2812	
			DATE MAILED:	08/01/01

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Application No.

lication No. Applicant(s) 09/692,211

Ishibashi et al

Examiner

Office Action Summary

S. Mulpuri

Art Unit **2812**



-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --Period for Reply A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status 1) X Responsive to communication(s) filed on IDS filed on 10/20/00 2a) This action is FINAL. 2b) X This action is non-final. 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11; 453 O.G. 213. Disposition of Claims is/are pending in the application. 4) X Claim(s) 1-12 4a) Of the above, claim(s) _______ is/are withdrawn from consideration. 5) Claim(s) is/are allowed. 6) X Claim(s) 1-12 is/are rejected. is/are objected to. 7) Claim(s) _____ are subject to restriction and/or election requirement. 8) Claims Application Papers 9) The specification is objected to by the Examiner. 10) The drawing(s) filed on is/are objected to by the Examiner. 11) The proposed drawing correction filed on is: a) approved b) disapproved. 12) The oath or declaration is objected to by the Examiner. Priority under 35 U.S.C. § 119 13) Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d). a) ☐ All b) ☐ Some* c) ☐ None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). *See the attached detailed Office action for a list of the certified copies not received. 14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e). Attachment(s) 18) Interview Summary (PTO-413) Paper No(s). 15) X Notice of References Cited (PTO-892) 19) Notice of Informal Patent Application (PTO-152) 16) Notice of Draftsperson's Patent Drawing Review (PTO-948) 17) 🔀 Information Disclosure Statement(s) (PTO-1449) Paper No(s). 5

Application/Control Number: 09692211

Art Unit:

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-12 are rejected under 35 U.S.C. 102(b) as being anticipated by Porowski et al.

Porowski et al discloses a method of making a semiconductor device by the following process steps: Providing a substrate, growing a first III-N layer at high pressure and high temperature "26"; and then growing a second III-N layer at low pressure and low temperature (see abstract), wherein III-N layers are GaN, AlN, InN containing Ga or Al or In (see abstract and examples)

Porowski et al further discloses growing a first III-N layer is at greater than atmospheric pressure as high as 10 Kbar; growing a second III-V layer depending on the temperature for example 900-1000 C, the pressure can lower than 1 bar, which is less tan atmospheric pressure(see col.8, lines 1-33).

It well known in the art indium containing III-V material growth needs high pressure to achieve significant incorporation during growth and high temperature gives good crystalline quality (see abstract in Yoshimoto et al from PTO892).

Art Unit:

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Prior art teach growing III-N layers.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Mulpuri whose telephone number is (703) 305-5184. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

SAVITRI MULPURI
PRIMARY EXAMINER